PEDMC:ejv 06/07/04 23-65037-01 13664-B 27532:

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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Larry C. Olsen et al.

**Application No. 10/726,744** 

Filed: December 2, 2003 Confirmation No. 6833

For: THERMOELECTRIC DEVICES AND

APPLICATIONS FOR THE SAME

Examiner: Not yet assigned

Art Unit: 1753

Attorney Reference No. 23-65037-01

#### **CERTIFICATE OF MAILING**

I hereby certify that this paper and the documents referred to as being attached or enclosed herewith are being deposited with the United States Postal Service as First Class Mail in an envelope addressed to: MAIL STOP AMENDMENT, COMMISSIONER FOR PATENTS, P.O. BOX 1450, ALEXANDRIA, VA 22313-1450 on the date shown below.

Attorney for Applicant(s)

Date Mailed (6/7/D)

# INFORMATION DISCLOSURE STATEMENT PURSUANT TO 37 C.F.R. § 1.97(b)(3)

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Listed on the accompanying form PTO-1449 and enclosed herewith are several English-language documents. Applicants respectfully request that these documents be listed as references cited on the issued patent.

If the present application was filed after June 30, 2003, copies of United States patents and United States published patent applications do not have to be provided to the Patent Office. This requirement of 37 C.F.R. § 1.98(a)(2)(i) has been waived by the United States Patent and Trademark Office pursuant to the Official Gazette Notice on August 5, 2003 (1276 OG 55). Applicants will provide copies of such patents upon request.

Applicants filed this Information Disclosure Statement ("IDS") before the mailing date of a first Office action on the merits. As a result, no fee should be required to file this IDS. However, if the Patent Office determines that a fee is required for Applicants to file this IDS, please charge any such fees, or credit overpayment, to Deposit Account No. 02-4550. A duplicate copy of this Information Disclosure Statement is enclosed.

The filing of this IDS shall not be construed to be an admission that the information cited in the statement is, or is considered to be, prior art or otherwise material to patentability as defined in 37 C.F.R. §1.56.

Respectfully submitted,

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Ву

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## BÉMATION DISCLOSURE STATEMENT BY APPLICANT

Attorney Docket Number	23-65037
Application Number	10/726,744
Filing Date	December 2, 2003
First Named Inventor	Larry C. Olsen
Art Unit	1753
Examiner Name	Not yet assigned

## U.S. PATENT DOCUMENTS

NOTE: If this application was filed after June 30, 2003, copies of United States patents and United States published patent applications do not have to be provided to the Patent Office. This requirement of 37 C.F.R. § 1.98(a)(2)(i) has been waived by the United States Patent and Trademark Office pursuant to the Official Gazette Notice on August 5, 2003 (1276 OG 55).

Examiner's Initials*	Cite No. (optional)	Number	Publication Date	Name of Applicant or Patentee
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<sup>\*</sup> Examiner: Initial if reference considered, whether or not in conformance with MPEP 609. Draw line through cite if not in conformance and not considered. Include copy of this form with next communication to applicant.

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	Examiner Name	Not yet assigned	
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